





# We generated a Band Diagram





We do the same thing again, starting with isolated atoms, Then turn on the bonding, then increase the number of interacti



**Fig. 7.29** Left: Energy levels of separated Mn and P atoms, Mn-P MO's from adjacent atoms, and extended bonding. Right: Band structure of a single  $[Mn_2P_2]_x^2$  layer. [Modified from Hoffmann, R.; Zheng, C. J. Phys. Chem. 1985, 89, 4175-4181. Reproduced with permission.]



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**Fig. 7.29** Left: Energy levels of separated Mn and P atoms, Mn-P MO's from adjacent atoms, and extended bonding. Right: Band structure of a single  $[Mn_2P_2]_{3}^{2-}$  layer. [Modified from Hoffmann, R.; Zheng, C. J. Phys. Chem. 1985, 89, 4175-4181. Reproduced with permission.]

#### An actual example, calculated using an M.O.theory

Mr



Fig. 7.30 Total DOS of the extended  $[Mn_2P_2]_x^2$  layer. The relative contributions of the manganese (dark area) and the phosphorus (light area) are indicated. Note that the bonding states at -19 and -15 eV are dominated by the phosphorus, that is, there is more electron density on the phosphorus than on the manganese. [From Hoffmann, R.; Zheng, C. J. Phys. Chem. 1985, 89, 4175-4181. Reproduced with permission.]

Mr

Polymeric unit

### MOT analogies with Band Diagram

- HOMO / LUMO and type of reactivity
- Valence Band / Conduction band and
- DE and Band Gap



More typically simplified to show only "frontier" bands:



## How Defects Improve Semi-Conduction



Gallium-Doping creates positive holes, as an acceptor band:

ΔE ~ 0.66 eV

A p-type semi-conductor

How Defects Improve Semi-Conduction

Pure Germanium

Arsenic-Doped Ge



Arsenic-Doping creates negative holes, as a donor band

 $\Delta E = 0.66 \text{ eV}$ 

An n-type semi-conductor

#### How Defects Lead to Device **N** Junctions = Diodes



Fermi level in n-type semi-conductor is at higher energy than for the p-type:

Spontaneous flow of electrons in one direction only.



Directional Flow of electrons --> current goes in one direction only

